

# **S20U60FCT**

# **Trench MOS Schottky Rectifier**

REVERSE VOLTAGE - 60 Volts FORWARD CURRENT - 20.0 Amperes

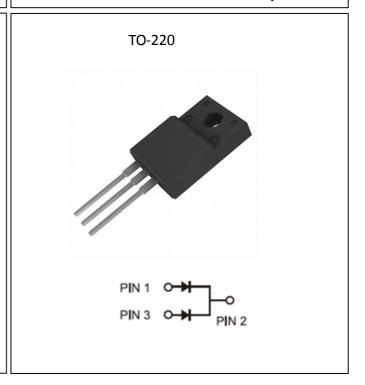
### **FEATURES**

- · Low power loss, high efficiency
- Low forward voltage drop
- High forward surge capability
- High frequency operation
- Excellent high temperature stability
- Trench MOS Schottky technology

### **MECHANICAL DATA**

Case: TO-220FPolarity: As marked

Weight: Approximated 1.6 grams



### MAXIMUM RATINGS AND ELECTRICAL CHARACTERISTICS

Ratings at 25<sup>°</sup>C ambient temperature unless otherwise specified.

Single phase, half wave, 60Hz, resistive or inductive load.

For capacitive load. derate current by 20%

Characteristics	Symbol	Value		Unit
Maximum Repetitive Peak Reverse Voltage	$V_{RRM}$	60		V
RMS Reverse Voltage	$V_{RMS}$	42		V
Forward Voltage Drop $I_F=5A  (T_J=25^{\circ}C)$ $I_F=5A  (T_J=125^{\circ}C)$	$V_{F}$	Typ. 0.43 0.35	Max. - -	V
I <sub>F</sub> =10 A (T <sub>J</sub> =25°ℂ) I <sub>F</sub> =10 A (T <sub>J</sub> =125°ℂ)		0.53 0.47	0.6 0.52	
Maximum Reverse Current at Rated $V_{RRM}$ $T_J$ =25°C $T_J$ =125°C	I <sub>R</sub>	Typ. 30 12	Max. 150 40	μA mA
Maximum Average Forward Rectified Current Total device Per diode	Io	20 10		А
Peak Forward Surge Current, 8.3 ms Single Half Sine-wave Superimposed on Rated Load (JEDEC method)	I <sub>FSM</sub>	150		А
Peak Repetitive Reverse Current at tp=2 µs, 1 kHz,	I <sub>RRM</sub>	1.0		Α
Operating and StorageTemperature Range	$T_{J,} T_{STG}$	-65 to +150		°C





## **Rating and Characteristic Curves**

